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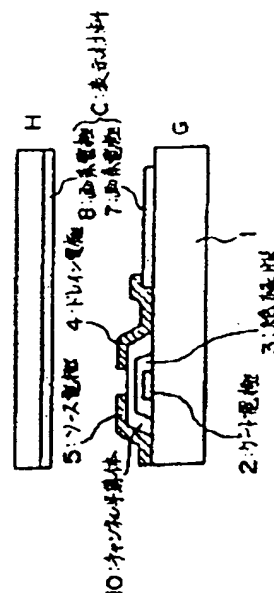
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TITLE : FIELD EFFECT TRANSISTOR,
 DISPLAY DEVICE USING THE SAME
 AND MANUFACTURE THEREOF



ABSTRACT : PURPOSE: To enable the manufacturing processes of the title display device to be simplified for enhancing the productivity by adopting the high molecular film as the material for a channel semiconductor and a gate insulating film.

CONSTITUTION: A gate electrode 2 is formed by patterning step on a high molecular substrate 1. At this time, if a picture element electrode 7 is formed together with the gate electrode 2, a display device G is to be formed simultaneously. Next, a gate insulating film 3 and a channel semiconductor film 10 are formed. As for the gate insulating film 3, all sorts of insulating organic or inorganic high molecule can be adduced, and especially those formed by plasma polymerization step, etc., are preferable in terms of the film thickness control. On the other hand, as for the channel semiconductor film 10, so-called conductive high molecule such as polypyrrole, etc., is to be adopted. Through these procedures, the active matrix display device not only to be manufactured in simplified processes but also in excellent productivity can be manufactured.

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